

**In the Specification:**

Please replace the paragraph beginning at line 11 of page 12 with the following amended paragraph:

Fabrication of embodiments of the present invention as illustrated in **Figure 2** is schematically illustrated in **Figures 3A-3E**. As seen in **Figure 3A**, a substrate **110** is provided on which nitride based devices may be formed. In particular embodiments of the present invention, the substrate **110** may be an n-type silicon carbide (SiC) substrate that may be, for example, 4H polytype of silicon carbide. Other silicon carbide candidate polytypes include the 3C, 6H, and 15R polytypes. Appropriate SiC substrates are manufactured by, for example, Cree, Inc., of Durham, N.C., the assignee of the present invention, and methods for producing are described, for example, in U. S. Patent Nos. Re. 34,861; 4,946,547; 5,200,022; and 6,218,680, the contents of which are incorporated herein by reference in their entirety. Similarly, techniques for epitaxial growth of Group III nitrides have been described in, for example, U. S. Patent Nos. 5,210,051; 5,393,993; 5,523,589; and ~~5,292,501~~5,592,501, the contents of which are also incorporated herein by reference in their entirety.